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Silicon PNP Power Transistor

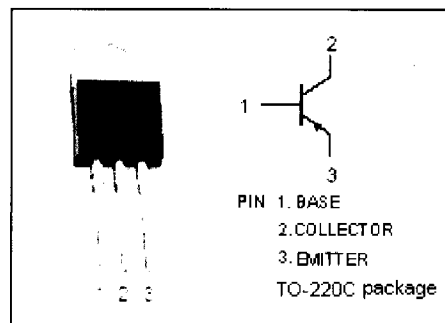
2SA1261

DESCRIPTION

- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -0.6V(\text{Max.}) @ I_C = -5A$
- Fast Switching Speed
- Complement to Type 2SC3157

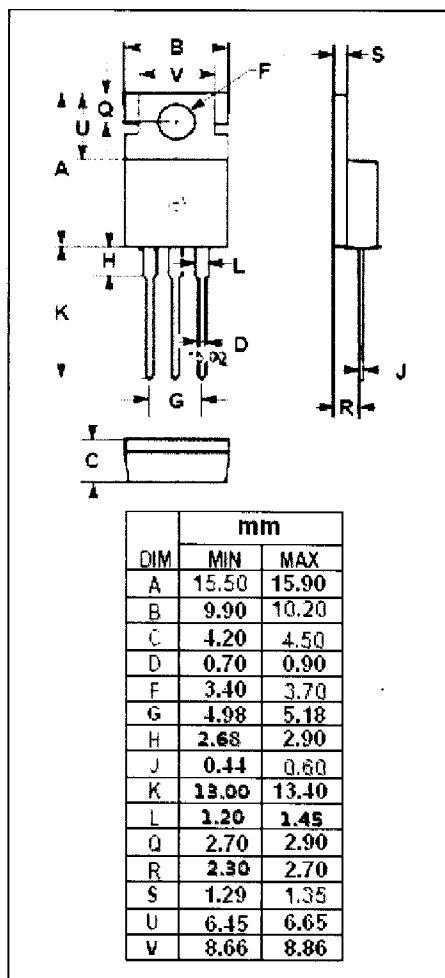
APPLICATIONS

- Developed for high-voltage high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high frequency power amplifiers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7.0	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-20	A
I_B	Base Current-Continuous	-3.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	60	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Silicon PNP Power Transistor

2SA1261

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -5.0A; I_B = -0.5A, L=1mH$	-100		V
$V_{CEX(SUS)-1}$	Collector-Emitter Sustaining Voltage	$I_C = -5.0A; I_{B1} = -I_{B2} = -0.5A, V_{BE(OFF)} = 5.0V, L=180\mu H, \text{clamped}$	-100		V
$V_{CEX(SUS)-2}$	Collector-Emitter Sustaining Voltage	$I_C = -10A; I_{B1} = -1.0A; I_{B2} = -0.5A, V_{BE(OFF)} = 5.0V, L=180\mu H, \text{clamped}$	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5.0A; I_B = -0.5A$		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5.0A; I_B = -0.5A$		-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100V; I_E = 0$		-10	μA
I_{CER}	Collector Cutoff Current	$V_{CE} = -100V; R_{BE} = 51\Omega, T_a = 125^\circ\text{C}$		-1.0	mA
I_{CEX}	Collector Cutoff Current	$V_{CE} = -100V; V_{BE(off)} = -1.5V$ $V_{CE} = -100V; V_{BE(off)} = -1.5V, T_a = 125^\circ\text{C}$		-10 -1.0	μA mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5V; I_C = 0$		-10	μA
h_{FE-1}	DC Current Gain	$I_C = -0.5A; V_{CE} = -5V$	40	200	
h_{FE-2}	DC Current Gain	$I_C = -3.0A; V_{CE} = -5V$	40	200	
h_{FE-3}	DC Current Gain	$I_C = -5.0A; V_{CE} = -5V$	20		

Switching times

t_{on}	Turn-on Time	$I_C = -5.0A, R_L = 10\Omega, I_{B1} = -I_{B2} = -0.5A, V_{CC} \approx -50V$		0.5	μs
t_{stg}	Storage Time			1.5	μs
t_f	Fall Time			0.5	μs

◆ h_{FE-2} Classifications

M	L	K
40-80	60-120	100-200